

General Description

The MDF10N65B MOSFET are produced using advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

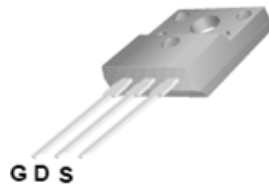
MDF10N65B is suitable device for SMPS, high Speed switching and general purpose applications.

Features

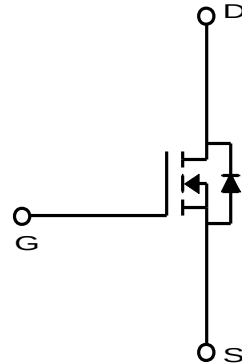
- $V_{DS} = 650V$
- $I_D = 10.0A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 1.0\Omega$ @ $V_{GS} = 10V$

Applications

- Power Supply
- PFC
- High Current, High Speed Switching



TO-220F
MDF Series



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	10.0*	A
	$T_C = 100^\circ C$		5.0*	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	40*	A
Power Dissipation	$T_C = 25^\circ C$	P_D	47.7	W
	Derate above 25 °C		0.38	W/°C
Repetitive Avalanche Energy ⁽¹⁾		E_{AR}	15	mJ
Peak Diode Recovery dv/dt ⁽³⁾		dv/dt	4.5	V/ns
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	347	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

* I_D limited by maximum junction temperature

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	2.62	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDF10N65BTH	-55~150°C	TO-220F	Tube	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	650	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 4A		0.85	1.0	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30V, I _D = 4A	-	10.6	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DS} = 520V, I _D = 8.0A, V _{GS} = 10V ⁽³⁾	-	29.3	-	nC
Gate-Source Charge	Q _{gs}		-	7.0	-	
Gate-Drain Charge	Q _{gd}		-	11.2	-	
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	1202	-	pF
Reverse Transfer Capacitance	C _{rss}		-	7.08	-	
Output Capacitance	C _{oss}		-	128.3	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 325V, I _D = 8.0A, R _G = 25Ω ⁽³⁾	-	19.4	-	ns
Rise Time	t _r		-	48	-	
Turn-Off Delay Time	t _{d(off)}		-	96.5	-	
Fall Time	t _f		-	49	-	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I _S		-	8	-	A
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 8.0A, V _{GS} = 0V	-	-	1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 8.0A, di/dt = 100A/μs	-	326	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	5.9	-	μC

Note :

1. Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$.
3. $I_{SD} \leq 10A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, $R_g = 25\Omega$, Starting $T_J = 25^\circ C$
4. $L = 6.4mH$, $I_{AS} = 10A$, $V_{DD} = 50V$, $R_g = 25\Omega$, Starting $T_J = 25^\circ C$.

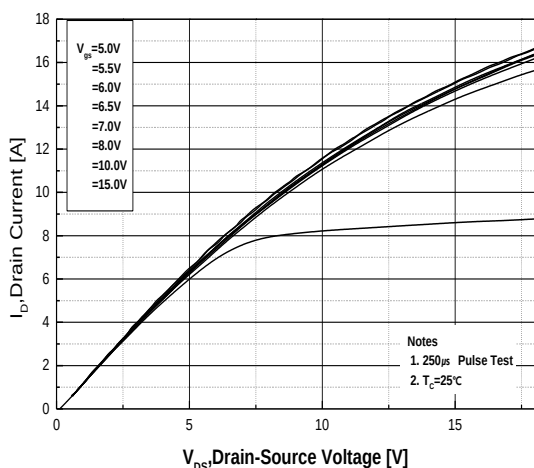


Fig.1 On-Region Characteristics

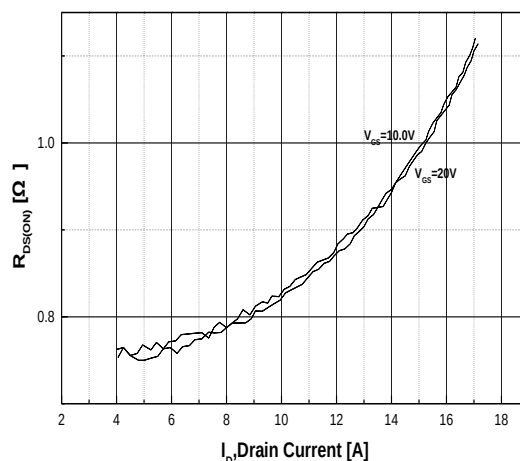


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

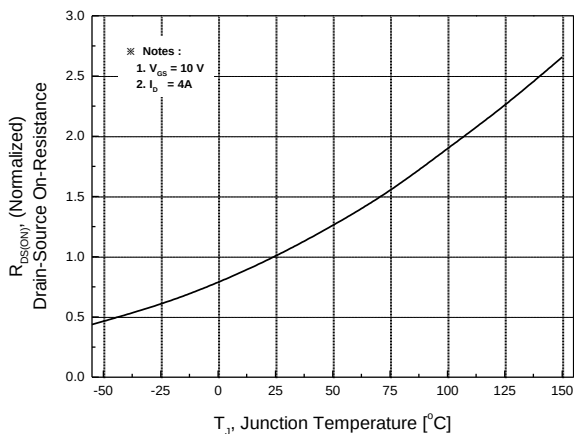


Fig.3 On-Resistance Variation with Temperature

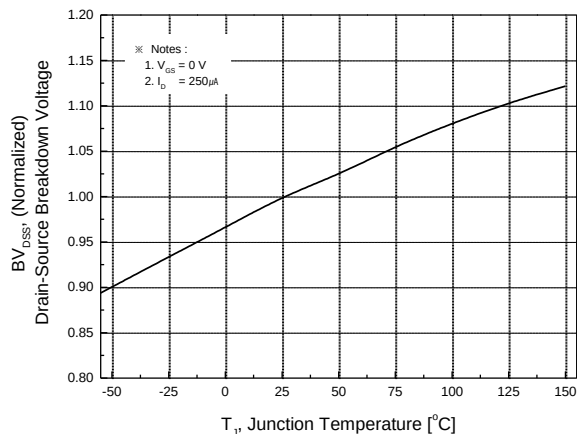


Fig.4 Breakdown Voltage Variation vs. Temperature

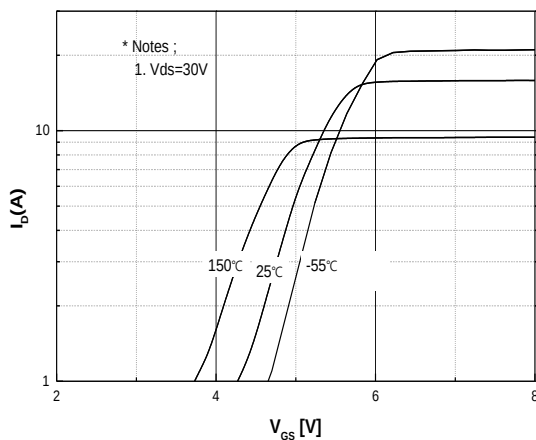


Fig.5 Transfer Characteristics

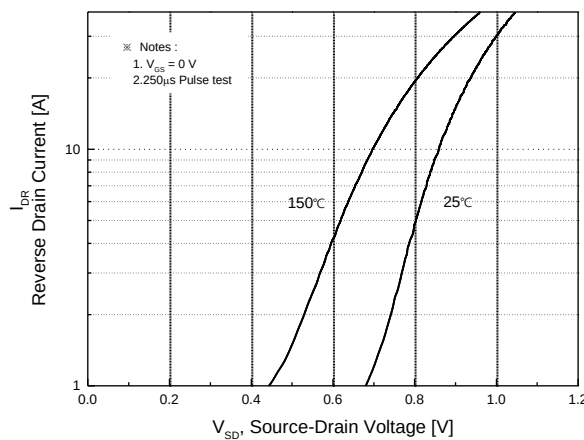
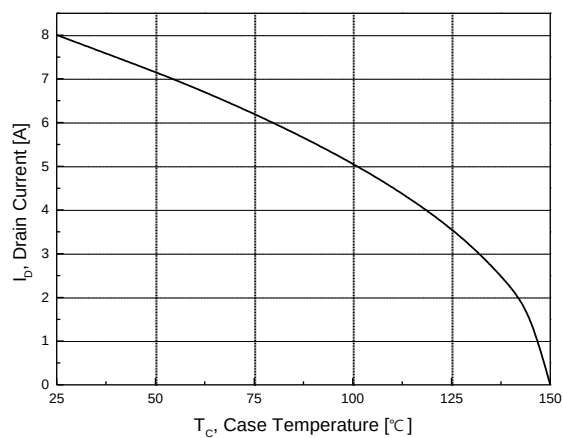
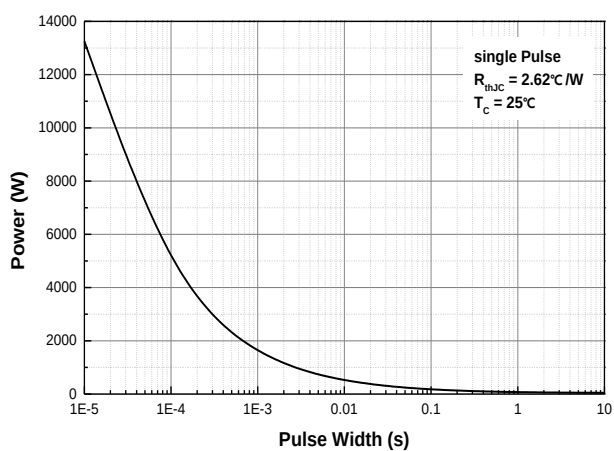
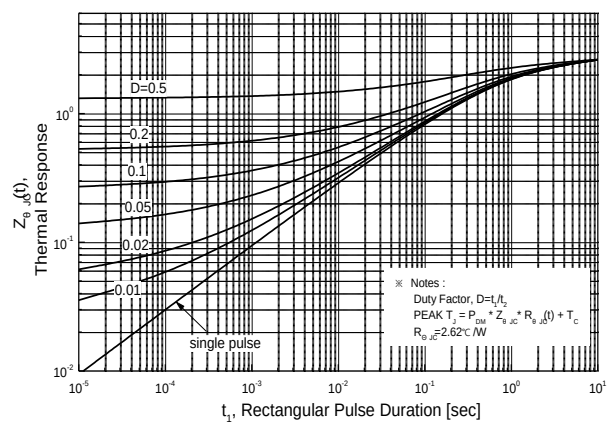
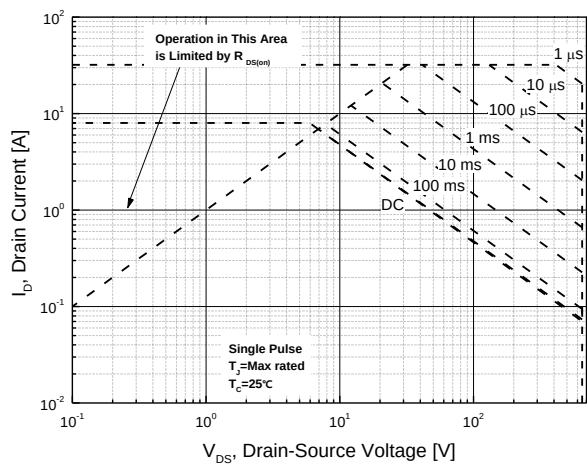
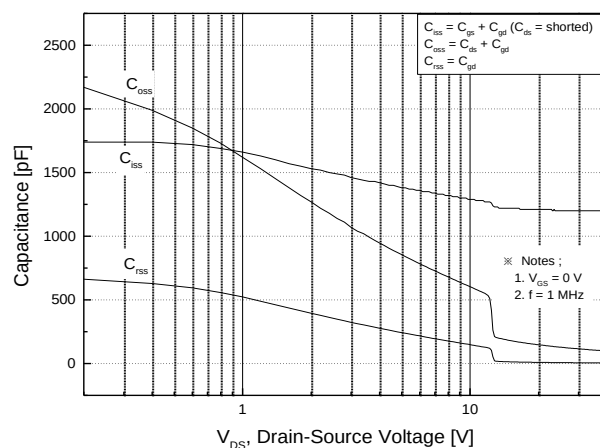
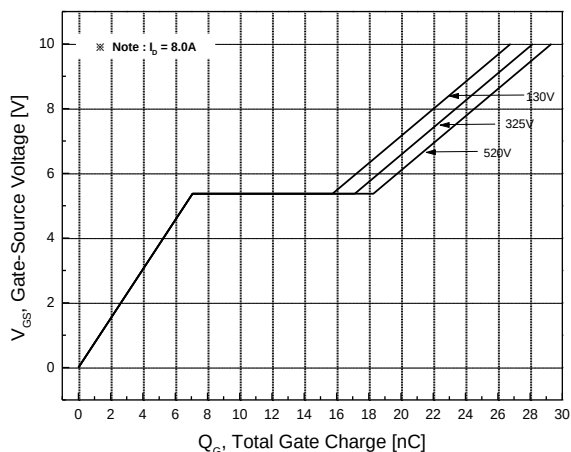


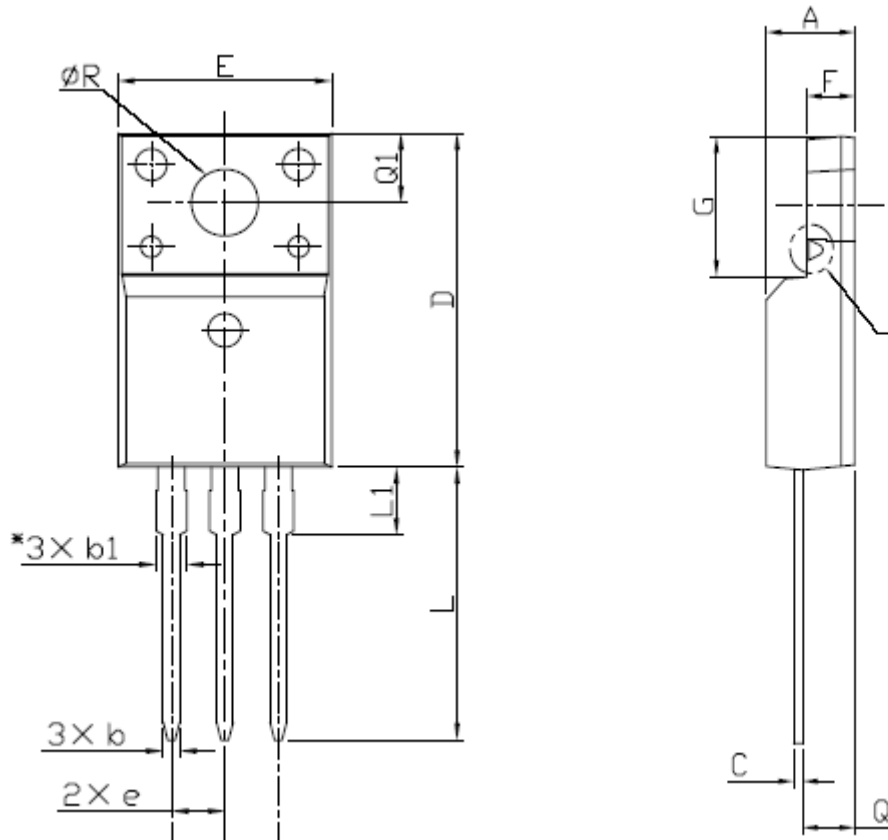
Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



Physical Dimensions

3 Leads, TO-220F

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	4.50		4.93
b	0.63		0.91
b1	1.15		1.47
C	0.33		0.63
D	15.47		16.13
E	9.60		10.71
e		2.54	
F	2.34		2.84
G	6.48		6.90
L	12.24		13.72
L1	2.79		3.67
Q	2.52		2.96
Q1	3.10		3.50
$\varnothing R$	3.00		3.55

Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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